

# Schottky barrier diode

## Pb - free package is available

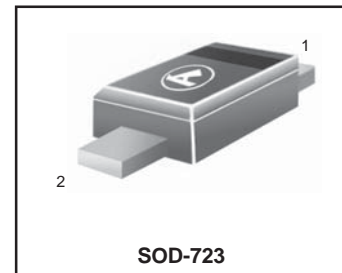
### ●Applications

Low current rectification

### ●Features

- 1) Ultra Small mold type.
- 2) Low  $I_R$ .
- 3) High reliability.

## LRB520G-30T1G

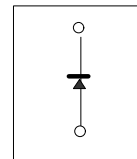


### ●Construction

Silicon epitaxial planar

### ●Device Marking

Device	Marking	Shipping
LRB520G-30T1G	E	4000/Tape&Reel



### ●Absolute maximum ratings (Ta=25°C)

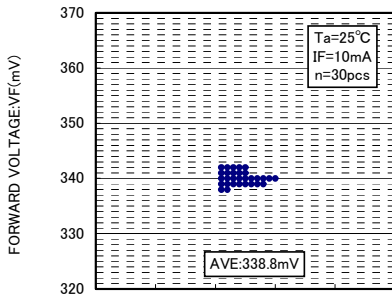
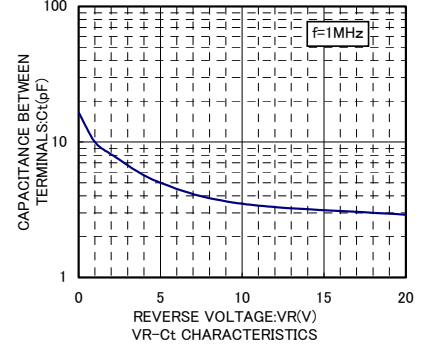
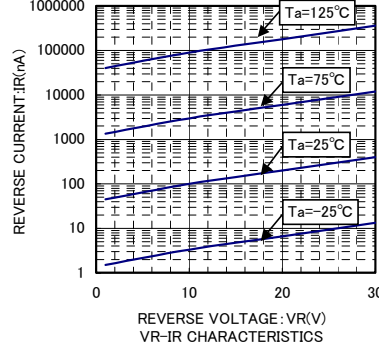
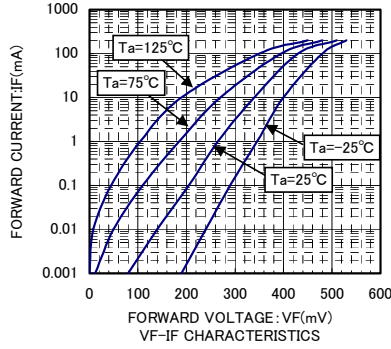
Parameter	Symbol	Limits	Unit
Reverse voltage(DC)	$V_R$	30	V
Average rectified forward current	$I_o$	100	mA
Forward current surge peak (60Hz·1cyc)	$I_{FSM}$	500	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

### ●Electrical characteristics (Ta=25°C)

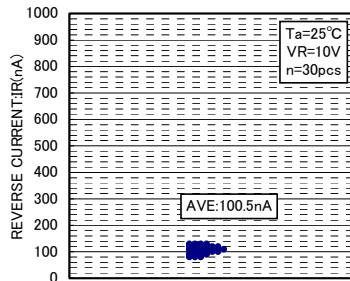
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.45	V	$I_F=10mA$
Reverse current	$I_R$	-	-	0.5	$\mu A$	$V_R=10V$

# LRB520G-30T1G

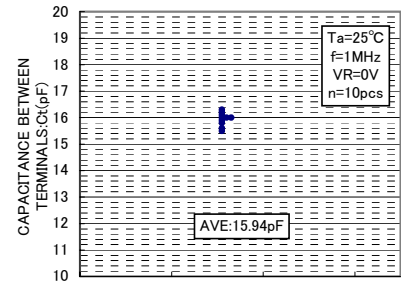
## Electrical characteristic curves (Ta=25°C)



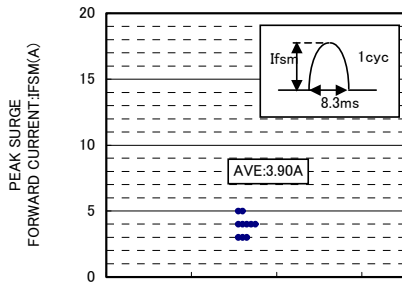
VF DISPERSION MAP



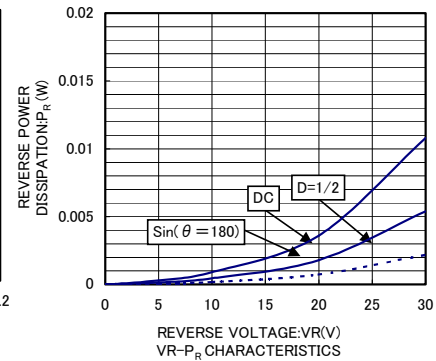
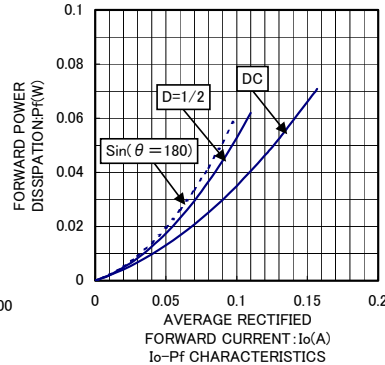
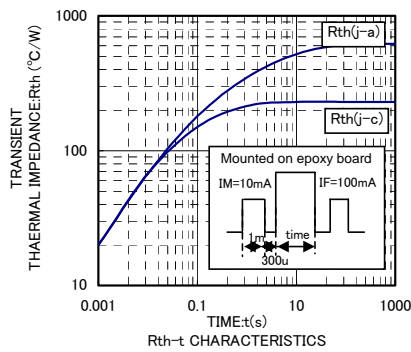
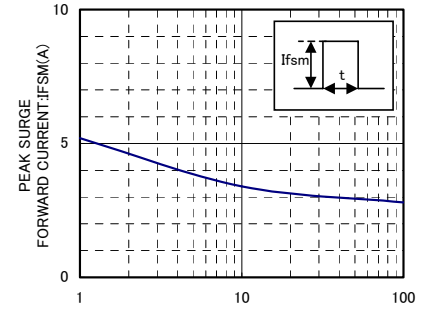
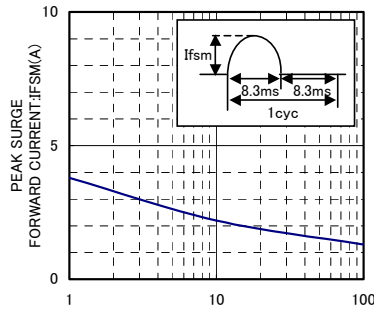
IR DISPERSION MAP



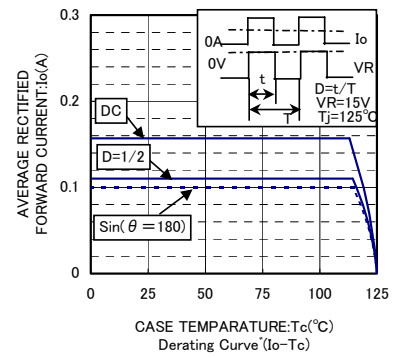
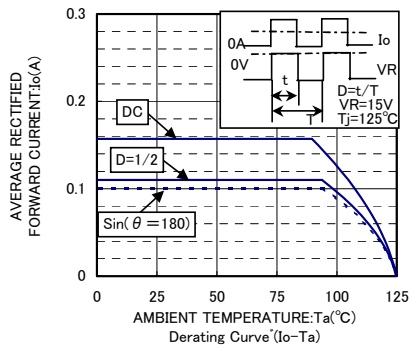
Ct DISPERSION MAP



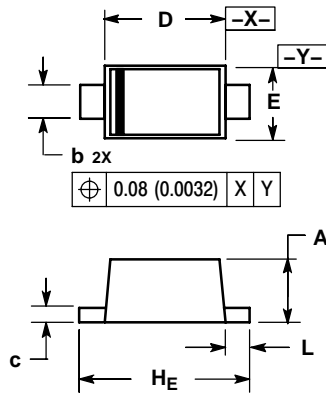
IFSM DISRESION MAP



# LRB520G-30T1G



# LRB520G-30T1G

**SOD-723**

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.20	0.25	0.006	0.0079	0.010

**SOLDERING FOOTPRINT\***
